

Silicon NPN Power Transistors

2SC4763

DESCRIPTION

- With TO-3P(H)IS package
- High speed ,high speed
- Low saturation voltage
- Bult-in damper diode

APPLICATIONS

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =300mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A; I _B =1.2A			5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A; I _B =1.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =1500V; I _E =0			1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0	83		250	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	8	12		
h _{FE-2}	DC current gain	I _C =6A ; V _{CE} =5V	5		9	
C _{ob}	Collector output capacitance	I _E =0 ; V _{CB} =10V, f=1MHz		170		pF
V _F	Diode forward voltage	I _F =6A		1.3	1.8	V
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V	1	3		MHz

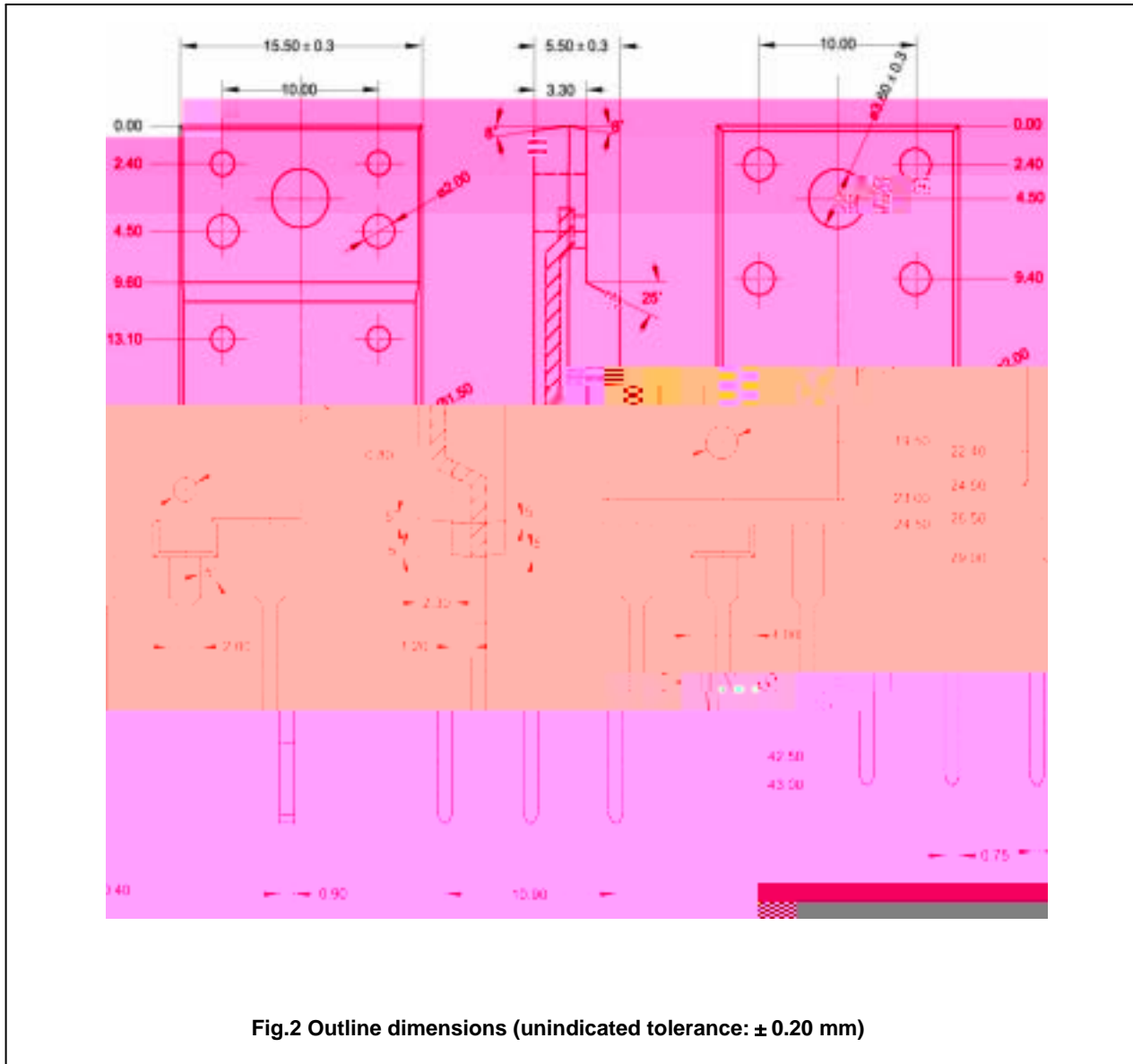
Switching times resistive load

t _s	Storage time	I _{CP} =6A; I _{B1} =1.2A I _{B2} =-2.4A; R _L =33		1.8	3.0	μs
t _f	Fall time			0.1	0.2	μs

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PACKAGE OUTLINE



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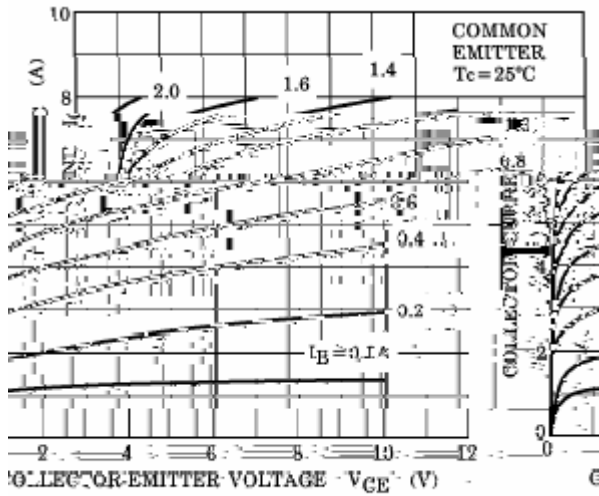


Fig.3 Static Characteristic

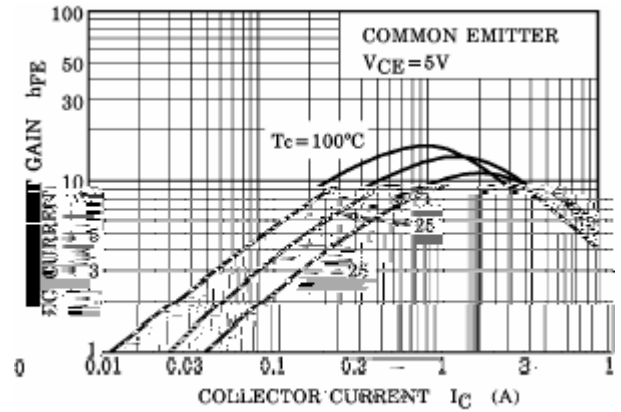


Fig.4 DC current Gain

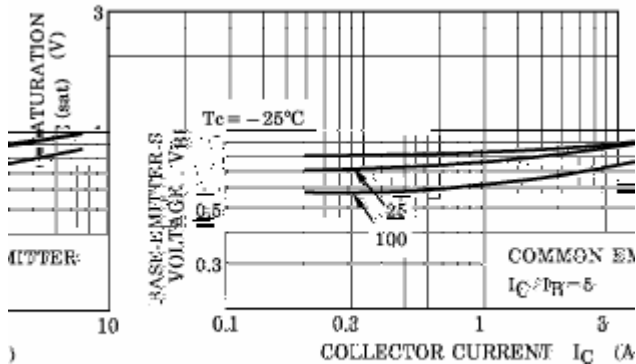


Fig.5 Base-Emitter Saturation Voltage

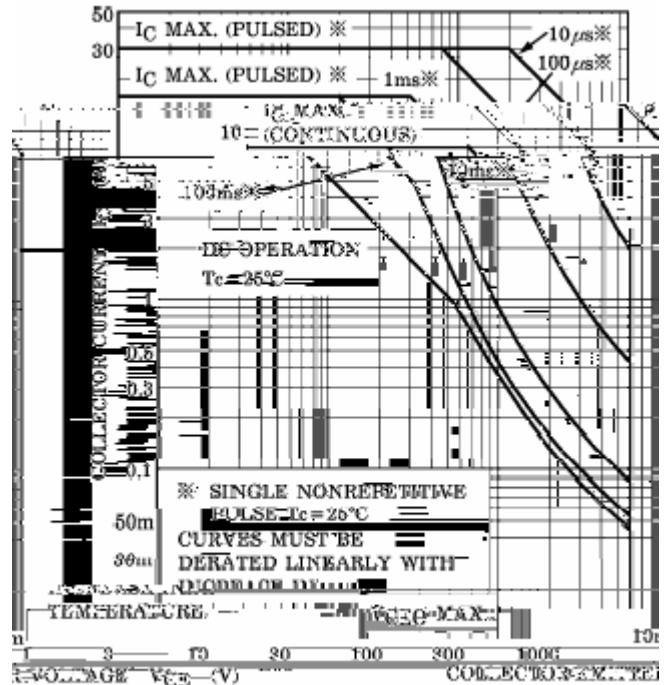


Fig.6 Safe Operating Area